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- Member of the Texas Instruments
  Widebus™ Family
- EPIC ™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

#### description

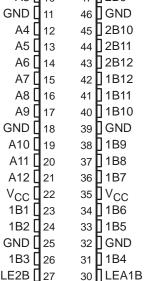
This 12-bit to 24-bit multiplexed D-type latch is designed for 1.65-V to 3.6-V<sub>CC</sub> operation.

The SN74ALVCH16260 is used in applications in which two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing address and data information in microprocessor or bus-interface applications. This device also is useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable (OE1B, OE2B, and OEA) inputs control the bus transceiver functions. The OE1B and OE2B control signals also allow bank control in the A-to-B direction.

#### (TOP VIEW) 56 OE2B OEA l LE1B 2 55 LEA2B 2B3 🛮 3 54 **∏** 2B4 GND ∏4 53 | GND 2B2 **[**] 5 52 2B5 2B1 **6** 51 **1**2B6 50 DV<sub>CC</sub> V<sub>CC</sub> 47 A1 **∏** 8 49 **1** 2B7 A2 🛮 9 48 1 2B8 A3 10 47 2B9 46 GND

DGG OR DL PACKAGE



SEL ∏28

29 OE1B

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16260 is characterized for operation from -40°C to 85°C.



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## **SN74ALVCH16260** 12-BIT TO 24-BIT MULTIPLEXED D-TYPE LATCH WITH 3-STATE OUTPUTS SCES046E – JULY 1995 – REVISED FEBRUARY 1999

#### **Function Tables**

## B TO A ( $\overline{OEB} = H$ )

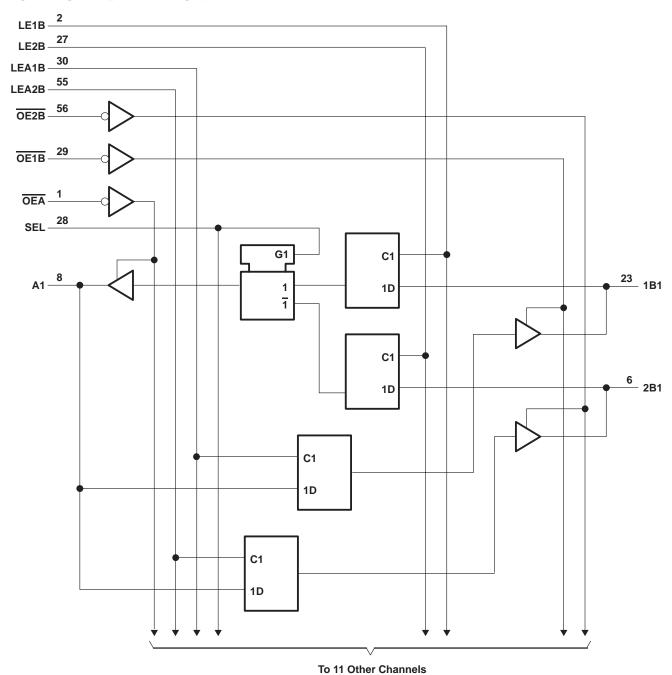
	INPUTS							
1B	2B	SEL	LE1B	LE2B	OEA	Α		
Н	Χ	Н	Н	Χ	L	Н		
L	Χ	Н	Н	X	L	L		
Х	Χ	Н	L	X	L	A <sub>0</sub>		
Х	Н	L	X	Н	L	Н		
Х	L	L	X	Н	L	L		
Х	Χ	L	X	L	L	A <sub>0</sub>		
Х	Χ	Χ	X	X	Н	Z		

## A TO B ( $\overline{OEA} = H$ )

		INPUTS			OUTI	PUTS
Α	LEA1B	LEA2B	OE1B	OE2B	1B	2B
Н	Н	Н	L	L	Н	Н
L	Н	Н	L	L	L	L
Н	Н	L	L	L	Н	2B <sub>0</sub>
L	Н	L	L	L	L	2B <sub>0</sub>
Н	L	Н	L	L	1B <sub>0</sub>	Н
L	L	Н	L	L	1B <sub>0</sub>	L
Х	L	L	L	L	1B <sub>0</sub>	2B <sub>0</sub>
Х	X	Χ	Н	Н	Z	Z
Х	Χ	X	L	Н	Active	Z
Х	Χ	X	Н	L	Z	Active
Х	X	Χ	L	L	Active	Active



## logic diagram (positive logic)



### SN74ALVCH16260 12-BIT TO 24-BIT MULTIPLEXED D-TYPE LATCH WITH 3-STATE OUTPUTS

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	
Input voltage range, V <sub>I</sub> : Except I/O ports (see Note 1)	
I/O ports (see Notes 1 and 2)	0.5 V to V <sub>CC</sub> + 0.5 V
Output voltage range, V <sub>O</sub> (see Notes 1 and 2)	$\dots$ -0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	–50 mA
Continuous output current, I <sub>O</sub>	±50 mA
Continuous current through each V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3): DGG package	81°C/W
DL package	
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
  - 2. This value is limited to 4.6 V maximum.
  - 3. The package thermal impedance is calculated in accordance with JESD 51.

#### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
Vcc	Supply voltage		1.65	3.6	V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		
$V_{IH}$	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		
	H High-level input voltage  Low-level input voltage  Input voltage Output voltage  High-level output current  Low-level output current	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	
$V_{IL}$		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	
٧ı	Input voltage		0	Vcc	V
٧o	Output voltage		0	Vcc	V
		V <sub>CC</sub> = 1.65 V		-4	
1	$\begin{array}{c} V_{\text{CC}} = 1.65 \ \forall \text{ to } 1.95 \ \forall \\ 0.65 \times V_{\text{CC}} \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 2.7 \ \forall \\ \hline V_{\text{CC}} = 2.7 \ \forall \text{ to } 3.6 \ \forall \\ \hline V_{\text{CC}} = 2.7 \ \forall \text{ to } 3.6 \ \forall \\ \hline V_{\text{CC}} = 2.7 \ \forall \text{ to } 3.6 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 1.65 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 1.65 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \text{ to } 1.95 \ \forall \\ \hline V_{\text{CC}} = 2.7 \ \forall \text{ to } 3.6 \ \forall \\ \hline V_{\text{CC}} = 2.7 \ \forall \text{ to } 3.6 \ \forall \\ \hline V_{\text{CC}} = 2.3 \ \forall \\ \hline V_{\text{CC}} = 2.7 $		-12	4	
ЮН		-12	mA		
		V <sub>CC</sub> = 3 V		3.6 CC 0.35 × V <sub>CC</sub> 0.7 0.8 V <sub>CC</sub> V <sub>CC</sub> -4 -12	
		V <sub>CC</sub> = 1.65 V		4	
la.	Low lovel output ourrent	V <sub>CC</sub> = 2.3 V		12	mA
IOL	Low-level output current	V <sub>CC</sub> = 2.7 V		12	IIIA
		V <sub>CC</sub> = 3 V		24	
Δt/Δν	Input transition rise or fall rate			10	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

NOTE 4: All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAI	RAMETER	TEST C	ONDITIONS	vcc	MIN	TYP†	MAX	UNIT
		I <sub>OH</sub> = -100 μA		1.65 V to 3.6 V	V <sub>CC</sub> -0.	.2		
VOH  VOL  II  I(hold)  IOZ  ICC  ΔICC  Ci  Control inputs	I <sub>OH</sub> = -4 mA		1.65 V	1.2				
	I <sub>OH</sub> = -6 mA	2.3 V	2					
Vон				2.3 V	1.7			V
		I <sub>OH</sub> = -12 mA		2.7 V	2.2			
				3 V	2.4			
		I <sub>OH</sub> = -24 mA		3 V	2			
		I <sub>OL</sub> = 100 μA		1.65 V to 3.6 V			0.2	
		I <sub>OL</sub> = 4 mA		1.65 V			0.45	
Voi		$I_{OL} = 6 \text{ mA}$		2.3 V			0.4	V
VOL		I <sub>OL</sub> = 12 mA		2.3 V			0.7	V
		IOL = 12 IIIA		2.7 V			0.4	
		I <sub>OL</sub> = 24 mA		3 V			0.55	
Ц		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ
		V <sub>I</sub> = 0.58 V		1.65 V	25			
		V <sub>I</sub> = 1.07 V		1.65 V	-25			
		V <sub>I</sub> = 0.7 V		2.3 V	45			
I <sub>I(hold)</sub>		V <sub>I</sub> = 1.7 V		2.3 V	-45			μΑ
		V <sub>I</sub> = 0.8 V		3 V	75			
		V <sub>I</sub> = 2 V		3 V	-75			
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500	
loz§		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ
ICC		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ
∆lcc		One input at V <sub>CC</sub> – 0.6 V,	Other inputs at $V_{\hbox{\footnotesize CC}}$ or GND	3 V to 3.6 V			750	μΑ
Ci	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3.5		pF
C <sub>io</sub>	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		9		pF

#### timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

		V <sub>CC</sub> =	1.8 V	V <sub>CC</sub> =	2.5 V 2 V	V <sub>CC</sub> =	2.7 V	V <sub>CC</sub> =	3.3 V 3 V	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>W</sub>	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	¶		3.3		3.3		3.3		ns
t <sub>su</sub>	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B	¶	·	1.4		1.1		1.1		ns
t <sub>h</sub>	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B	¶		1.6		1.9		1.5		ns

 $<sup>\</sup>P$  This information was not available at the time of publication.



<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $<sup>\</sup>$  For I/O ports, the parameter IOZ includes the input leakage current.

## SN74ALVCH16260 12-BIT TO 24-BIT MULTIPLEXED D-TYPE LATCH WITH 3-STATE OUTPUTS

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# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> =	2.5 V 2 V	VCC =	2.7 V	V <sub>CC</sub> =	3.3 V 3 V	UNIT
	(INFOT)	(001F01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
	A or B	B or A	†	1	5.4		5.1	1.2	4.3	
<sup>t</sup> pd	LE	A or B	†	1	5.6		5.2	1	4.4	ns
	SEL	А	†	1	6.9		6.6	1.1	5.6	
t <sub>en</sub>	ŌĒ	A or B	†	1	6.7		6.4	1	5.4	ns
<sup>t</sup> dis	ŌĒ	A or B	†	1	5.7		5	1.3	4.6	ns

<sup>†</sup> This information was not available at the time of publication.

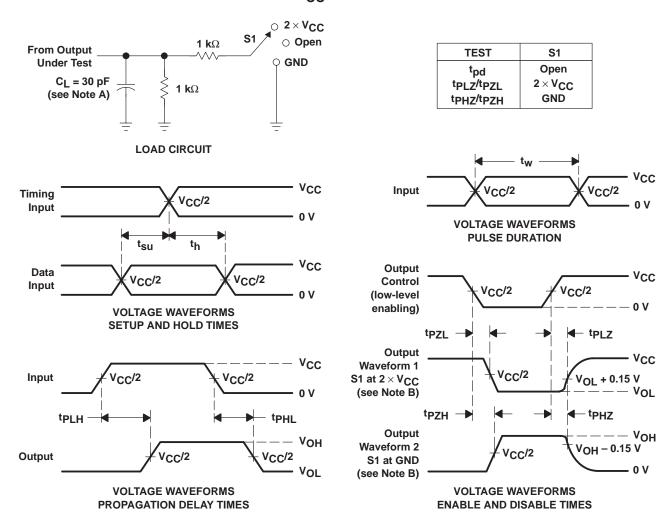
## operating characteristics, $T_A = 25^{\circ}C$

PARAMETER			TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	UNIT	
FARAWETER		TEST CONDITIONS	TYP	TYP	TYP	UNIT		
Power dissipation		All outputs enabled	C <sub>1</sub> = 50 pF. f = 10 MHz	Ť	37	41	pF	
Cpd	capacitance	All outputs disabled	$C_L = 50 \text{ pF},  f = 10 \text{ MHz}$	†	4	7	PΓ	

<sup>†</sup> This information was not available at the time of publication.



# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V}$



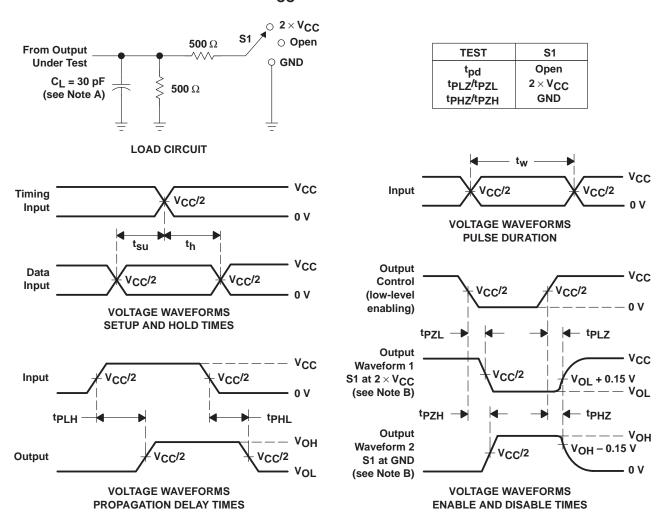
NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms

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## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



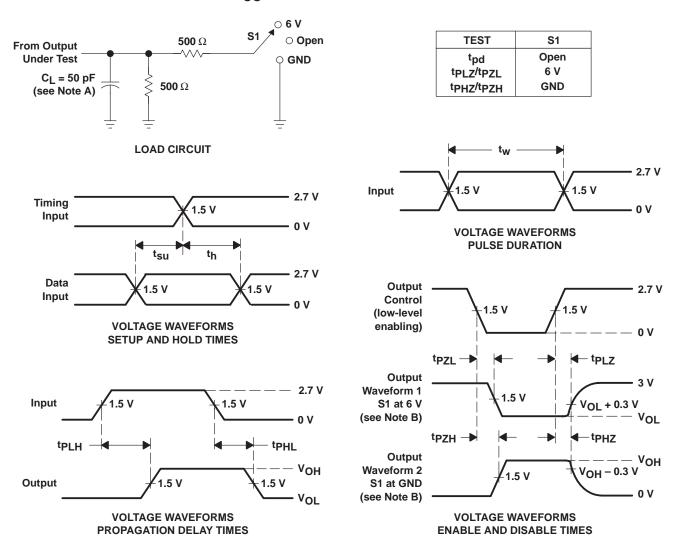
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzl and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.7 \text{ V}$ AND 3.3 V $\pm$ 0.3 V



NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzi and tpzH are the same as ten.
- G. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>pd</sub>.

Figure 3. Load Circuit and Voltage Waveforms



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